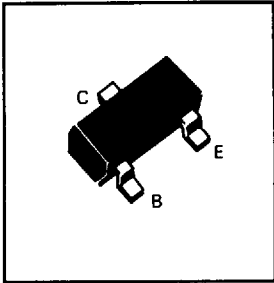


SOT23 PNP SILICON PLANAR
HIGH VOLTAGE TRANSISTOR

HT3

PARTMARKING DETAIL:
HT3 - 3T



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-90	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-100	mA
Power Dissipation at $T_{amb} = 25^{\circ}C$	P_{TOT}	330	mW
Operating and Storage Temperature Range	$t_j:tstg$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-90			V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80			V	$I_C = -2mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -10\mu A$
Collector Cut-Off Current	I_{CBO}			-100	nA	$V_{CB} = -80V, I_E = 0$
	I_{CES}			-100 -5	nA μA	$V_{CE} = -80V, V_{BE} = 0$ $V_{CE} = -80V, V_{BE} = 0$ $T_j = 125^{\circ}C$
	I_{CEX}			-10	μA	$V_{CE} = -80V$ $V_{BE} = -0.2V, T_j = 85^{\circ}C$
	I_{EBO}			-200	nA	$V_{BE} = -4V$
Static Forward Current Transfer Ratio	h_{FE}	30 35 50 30				$I_C = -100\mu A, V_{CE} = -1V$ $I_C = -1mA, V_{CE} = -1V$ $I_C = -10mA, V_{CE} = -1V$ $I_C = -50mA, V_{CE} = -1V$
Collector-Emitter Voltage	$V_{CE(sat)}$			-750	mV	$I_C = -50mA, I_B = -5mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	$I_C = -50mA, I_B = -5mA$
Output Capacitance	C_{obo}			10	pF	$V_{CB} = -10, I_E = 0$ $f = 1MHz$
Transition Frequency	f_T	50			MHz	$V_{CE} = -5V, I_C = -10mA,$ $f = 10MHz$
Switching Times	t_{on}			500	ns	$I_C = -10mA$
	t_{off}			1000	ns	$I_{B1} = I_{B2} = -1mA$